

For SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON

**PRELIMINARY AMENDMENT A**

SIR:

In the Title:

SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY  
DEVICE LAYER AND A PROCESS FOR THE PREPARATION THEREOF.

In the Specification:

Please replace the paragraph beginning on page 1, line 3 with the following rewritten paragraph:

This application claims priority from U.S. provisional application Serial No. 60/098,902, filed on September 2, 1998, U.S. application Serial Number 09/387,288 filed on August 31,